



CSD13381F4, 12 V N-Channel FemtoFET™ MOSFET

1 Features

- Low On Resistance
- Low Q_g and Q_{gd}
- Low Threshold Voltage
- Ultra-Small Footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Ultra-Low Profile
 - 0.35 mm Height
- Integrated ESD Protection Diode
 - Rated > 4 kV HBM
 - Rated > 2 kV CDM
- Lead and Halogen Free
- RoHS Compliant

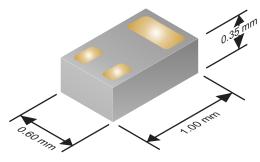
2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching Applications
- Single-Cell Battery Applications
- Handheld and Mobile Applications

3 Description

The FemtoFET[™] MOSFET technology is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

Typical Part Dimensions



Product Summary

V _{DS}	Drain-to-Source Voltage	12		V
Qg	Gate Charge Total (4.5V)	1060		рС
Q_{gd}	Gate Charge Gate to Drain	140		рС
		$V_{GS} = 1.8V$	310	
R _{DS(on)}	Drain-to-Source On Resistance	$V_{GS} = 2.5 V$	170	mΩ
		$V_{GS} = 4.5 V$	140	
V _{GS(th)}	Threshold Voltage	0.85		V

Ordering Information

Device	Qty	Media	Package	Ship					
CSD13381F4	3000	7-Inch Reel	Femto (0402) 1.0 mm x 0.6 mm	Tape and					
CSD13381F4T	250	7-Inch Reel	SMD Lead Less	Reel					

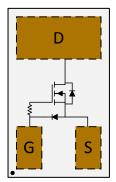
Absolute Maximum Ratings

T _A = 25	°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	12	V
V _{GS}	Gate-to-Source Voltage	8	V
I _D	Continuous Drain Current, $T_A = 25^{\circ}C^{(1)}$	2.1	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	7	А
	Continuous Gate Clamp Current	35	mA
I _G	Pulsed Gate Clamp Current ⁽²⁾	350	ША
PD	Power Dissipation ⁽¹⁾	500	mW
ESD	Human Body Model (HBM)	4	kV
Rating	Charged Device Model (CDM)	2	kV
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 7.4 A, L = 0.1 mH, R_G = 25 Ω	2.7	mJ

⁽¹⁾ Typical $R_{\theta JA}$ = 90°C/W on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration \leq 300 µs, duty cycle \leq 2%

Top View





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

4 Specifications

4.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics					
BV _{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 V, I_{DS} = 250 \mu A$	12			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 9.6 V			100	nA
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 4 V			50	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \ \mu A$	0.65	0.85	1.10	V
		V _{GS} = 1.8 V, I _{DS} =0.5 A		310	400	mΩ
R _{DS(on)}	Drain-to-Source On Resistance	$V_{GS} = 2.5 \text{ V}, \text{ I}_{DS} = 0.5 \text{ A}$		170	225	mΩ
		V _{GS} = 4.5 V, I _{DS} = 0.5 A		140	180	mΩ
9 _{fs}	Transconductance	V _{DS} = 6 V, I _{DS} = 0.5 A		3.2		S
Dynamic	c Characteristics					
C _{iss}	Input Capacitance			155	200	pF
C _{oss}	Output Capacitance	$V_{GS} = 0 V, V_{DS} = 6 V,$ f = 1 MHz		47	62	pF
C _{rss}	Reverse Transfer Capacitance			2.5	3.3	pF
R_G	Series Gate Resistance			23		Ω
Qg	Gate Charge Total (4.5 V)			1060	1400	рС
Q _{gd}	Gate Charge Gate to Drain			140		рС
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 6 \text{ V}, \text{ I}_{DS} = 0.5 \text{ A}$		230		рС
Q _{g(th)}	Gate Charge at V _{th}			155		рС
Q _{oss}	Output Charge	V _{DS} = 6 V, V _{GS} = 0 V		1120		рС
t _{d(on)}	Turn On Delay Time			3.7		ns
t _r	Rise Time	$V_{DS} = 0 V, V_{GS} = 4.5 V,$		1.5		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 0.5 \text{ A}, R_G = 2 \Omega$		11.0		ns
t _f	Fall Time			3.8		ns
Diode C	haracteristics					
V_{SD}	Diode Forward Voltage	I _{SD} = 0.5 A, V _{GS} = 0V		0.73	0.9	V
Q _{rr}	Reverse Recovery Charge			1550		рС
t _{rr}	Reverse Recovery Time	V_{DS} = 6 V, I _F = 0.5 A, di/dt = 300 A/µs		6		ns

4.2 Thermal Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

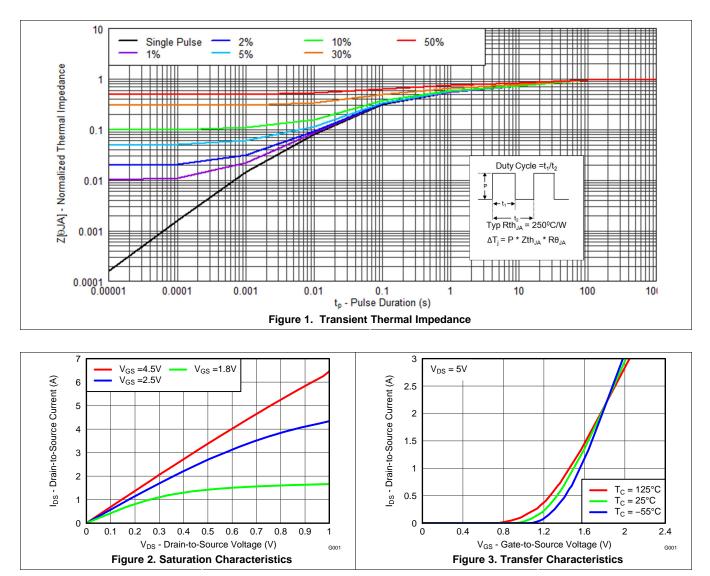
	PARAMETER	Typical Values	UNIT
Р	Junction-to-Ambient Thermal Resistance ⁽¹⁾	90	°C/W
R _{θJA}	Junction-to-Ambient Thermal Resistance ⁽²⁾	250	°C/W

Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
Device mounted on FR4 material with minimum Cu mounting area.



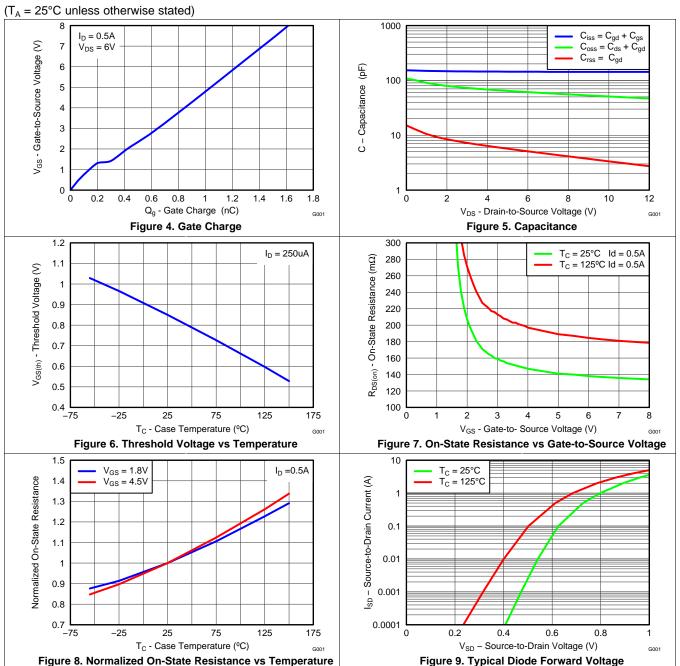
5 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



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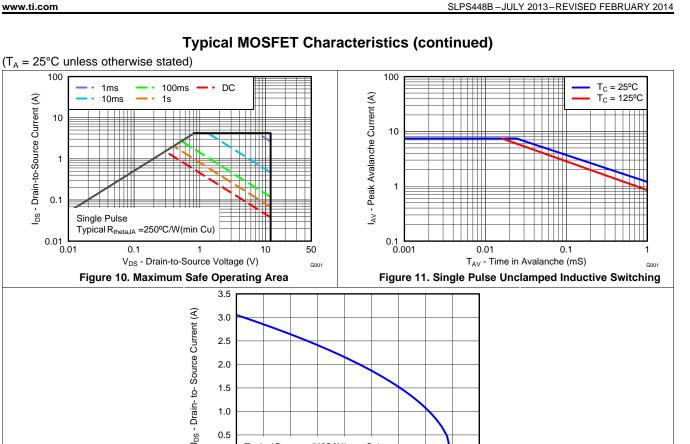
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Typical MOSFET Characteristics (continued)

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FRUMENTS



Typical R_{thetaJA} =90°C/W(max Cu)

25 50 75

T_A - AmbientTemperature (°C)

Figure 12. Maximum Drain Current vs Temperature

100 125 150 175

G00

1.5 1.0 0.5

0.0

-50

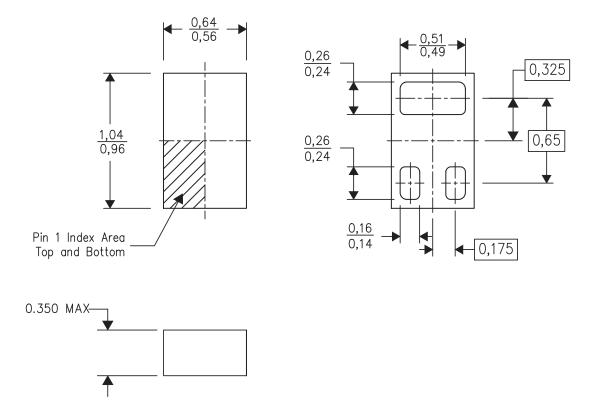
-25

0

CSD13381F4

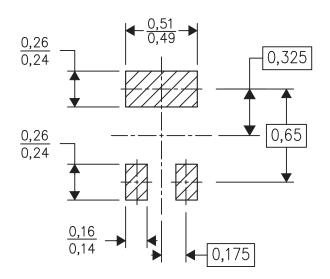
6 Mechanical Data

6.1 0402 Mechanical Dimensions



- (1) All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- (2) This drawing is subject to change without notice.
- (3) This package is a PB-free solder land design.

6.2 Recommended Minimum PCB Layout

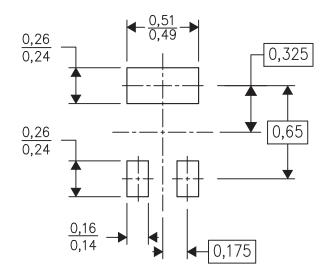


(1) All dimensions are in millimeters.

6

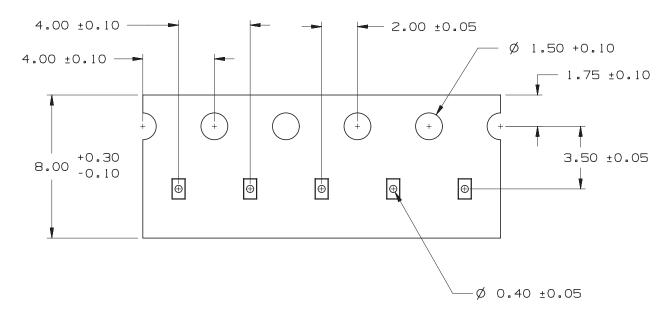


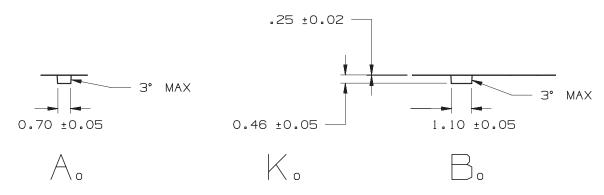
6.3 Recommended Stencil Pattern



(1) All dimensions are in millimeters.

6.4 CSD13381F4 Embossed Carrier Tape Dimensions





(1) Pin 1 is oriented in the top-right quadrant of the tape enclosure (quadrant 2), closest to the carrier tape sprocket holes.



7 Trademarks

FemtoFET is a trademark of Texas Instruments.

8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	Changes from Revision A (November 2013) to Revision B					
•	Added I _G parameter	1				
•	Lowered I _{DSS} limit	2				
•	Lowered I _{GSS} limit	2				

Changes from Original (July 2013) to Revision A

•	Updated title	1
•	Updated device ordering information	1
•	Changed test voltage conditions	2
•	Changed Figure 4 Gate Charge graph	4

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All d	imensions	are	nominal
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Device	•	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD13381F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

7-May-2014



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD13381F4	PICOSTAR	YJC	3	3000	182.0	182.0	17.0

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